

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Rule 53(b) Divisional Application of:

Taiji EMA et al.

Divisional of S.N. 09/637,256 filed August 14, 2000

Group Art Unit: To Be Assigned

Filed: Herewith

Examiner: To Be Assigned

For: SEMICONDUCTOR STORAGE DEVICE AND METHOD FOR FABRICATING THE  
SAME

**INFORMATION DISCLOSURE STATEMENT**  
**PURSUANT TO 37 CFR 1.97(b)**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

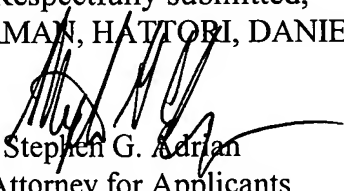
Date: March 11, 2004

Sir:

This Information Disclosure Statement is being filed in order to comply with Applicant's duty of disclosure under 37 CFR 1.56. The documents listed on the Form PTO-1449 were made of record in parent application Serial No. 09/637,256.

The Commissioner is authorized to charge our Deposit Account No. 50-2866 for any fee which is deemed by the Patent and Trademark Office to be required to effect consideration of this statement.

Respectfully submitted,  
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<b>INFORMATION</b>	Atty. Docket No. <b>960045E</b>		Serial No. <b>To be assigned</b>
	Applicant(s): <b>Taiji EMA et al.</b>		
	Filing Date: <b>Herewith</b>		Group Art Unit: <b>To be assigned</b>

PTO-1449

### U.S. PATENT DOCUMENTS

Examiner	Document No.	Name	Date	Class	Subclass	Filing Date
Initial						(If appropriate)
_____	AB	5,502,336	Park et al.			03/96
_____	AC	5,479,054	Tottori			12/95
_____	AD	5,338,700	Dennison et al.			08/94
_____	AE	4,974,040	Taguchi et al.			11/90
_____	AF	5,150,278	Gonzalez et al.			09/92
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_____	AH	5,605,857	Jost et al.			02/97
_____	AI	5,324,681	Lowrey et al.			06/94
_____	AJ	5,292,677	Dennison			03/94
_____	AK	5,281,549	Fazan et al.			01/94
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_____	AM					

### FOREIGN PATENT DOCUMENTS

Document No.	Date	Country	Translation
			(Yes or No)
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_____ AO 3-167874	07/19/91	Japan	
_____ AP 5-218332	08/27/93	Japan	
_____ AQ			

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_____	AT	M.F. CHISHOLM et al.; "A High Performance 0.5 um Five-Level Metal Process with Extendibility of Sub-Half Micron"; pages 22-28; June 1994.
_____	AU	M. RUTTEN et al.; "Pattern Density Effects in Tungsten CMP", Proceedings of 12 <sup>th</sup> International VMIC; pages 491-497; June 1995.
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_____	A W	T. KAGA et al.; "A 0.29-um <sup>2</sup> MIM-Crown Cell and Process Technologies for 1-Gigabit DRAMs"; Technical Digest of IEDM; pages 927-929; December 1994.
_____	AX	H.K. KANG et al.; "Highly Manufacturable Process Technology for Reliable 256 Mbit and 1 Gbit DRAMs"; Technical Digest of IEDM; pages 635-638; December 1994.
_____	A Y	Y. OHJI et al.; "Ta <sub>2</sub> O <sub>5</sub> Capacitors Dielectric Material for Giga-bit DRAMs"; Technical Digest of IEDM; pages 111-114; December 1995.
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_____	BA	K.P. LEE et al.; "A Preocess Technology for 1 Giga-bit DRAM"; Technical Digest of IEDM; pages 907-910; December 1995.
_____	BB	J.K. PARK et al.; "Isolation Merged Bit Line Cell(IMBC) for 1Gb DRAM and Beyond". Technical Digest of IEDM; pages911-914; December 1995.
_____	BC	
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Examiner

Date Considered